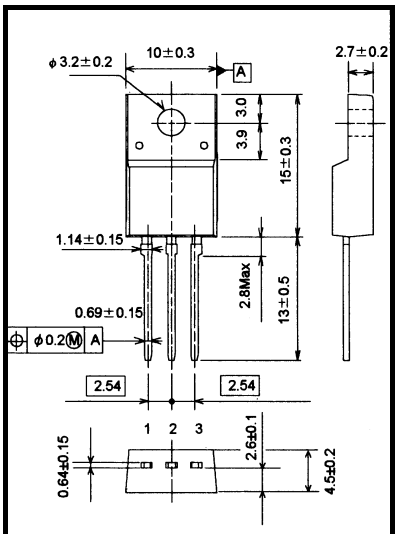
# TK15A60U

Switching Regulator Applications

Unit: mm




1: Gate
2: Drain
3: Source

| | |
|---|---|
| JEDEC | — |
| JEITA | SC-67 |
| TOSHIBA | 2-10U1B |

Weight: 1.7 g (typ.)

- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 0.24 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 8.5 S (typ.)
- Low leakage current: $I_{DSS}$ = 100 μA ($V_{DS}$ = 600 V)
- Enhancement mode: $V_{th}$ = 3.0 to 5.0 V ($V_{DS}$ = 10 V, $I_D$ = 1 mA)

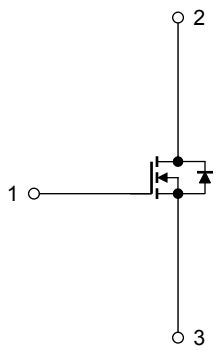
## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit |
|---|---|---|---|---|
| Drain-source voltage | | $V_{DSS}$ | 600 | V |
| Gate-source voltage | | $V_{GSS}$ | ±30 | V |
| Drain current | DC (Note 1) | $I_D$ | 15 | A |
| | Pulse (t = 1 ms) (Note 1) | $I_{DP}$ | 30 | |
| Drain power dissipation (Tc = 25°C) | | $P_D$ | 40 | W |
| Single pulse avalanche energy (Note 2) | | $E_{AS}$ | 81 | mJ |
| Avalanche current (Note 3) | | $I_{AR}$ | 15 | A |
| Repetitive avalanche energy | | $E_{AR}$ | 4 | mJ |
| Channel temperature | | $T_{ch}$ | 150 | °C |
| Storage temperature range | | $T_{stg}$ | -55 to 150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/''Derating Concept and Methods'') and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---|---|---|---|
| Thermal resistance, channel to case | $R_{th\ (ch-c)}$ | 3.125 | °C/W |
| Thermal resistance, channel to ambient | $R_{th\ (ch-a)}$ | 62.5 | °C/W |



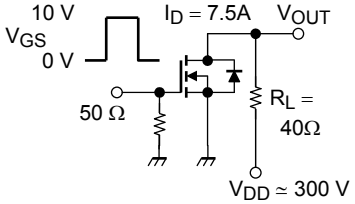

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}$ = 90 V, $T_{ch}$ = 25°C (initial), L = 0.63 mH, $R_G$ = 25 Ω, $I_{AR}$ = 15 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

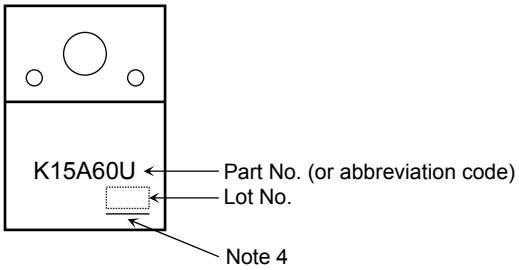
## Electrical Characteristics (Ta = 25°C)

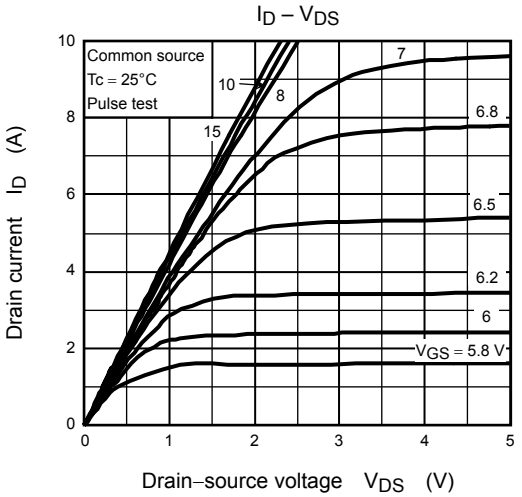
| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|---|
| Gate leakage current | | $I_{GSS}$ | $V_{GS}$ = ±30 V, $V_{DS}$ = 0 V | — | — | ±1 | μA |
| Drain cut-off current | | $I_{DSS}$ | $V_{DS}$ = 600 V, $V_{GS}$ = 0 V | — | — | 100 | μA |
| Drain-source breakdown voltage | | $V_{(BR)DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 600 | — | — | V |
| Gate threshold voltage | | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 1 mA | 3.0 | — | 5.0 | V |
| Drain-source ON-resistance | | $R_{DS(ON)}$ | $V_{GS}$ = 10 V, $I_D$ = 7.5 A | — | 0.24 | 0.3 | Ω |
| Forward transfer admittance | | $\|Y_{fs}\|$ | $V_{DS}$ = 10 V, $I_D$ = 7.5 A | 3.0 | 8.5 | — | S |
| Input capacitance | | $C_{iss}$ | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz | — | 950 | — | pF |
| Reverse transfer capacitance | | $C_{rss}$ | | — | 47 | — | |
| Output capacitance | | $C_{oss}$ | | — | 2300 | — | |
| Switching time | Rise time | $t_r$ |   Duty ≤ 1%, $t_w$ = 10 μs | — | 37 | — | ns |
| | Turn-ON time | $t_{on}$ | | — | 80 | — | |
| | Fall time | $t_f$ | | — | 8 | — | |
| | Turn-OFF time | $t_{off}$ | | — | 105 | — | |
| Total gate charge | | $Q_g$ | $V_{DD}$ ≈ 400 V, $V_{GS}$ = 10 V, $I_D$ = 15 A | — | 17 | — | nC |
| Gate-source charge | | $Q_{gs}$ | | — | 10 | — | |
| Gate-drain charge | | $Q_{gd}$ | | — | 7 | — | |

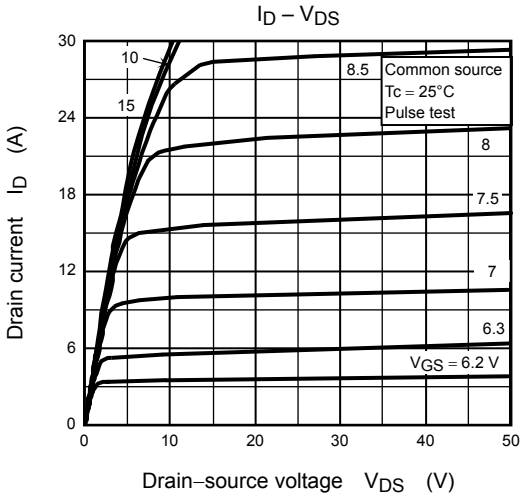
## Source-Drain Ratings and Characteristics (Ta = 25°C)

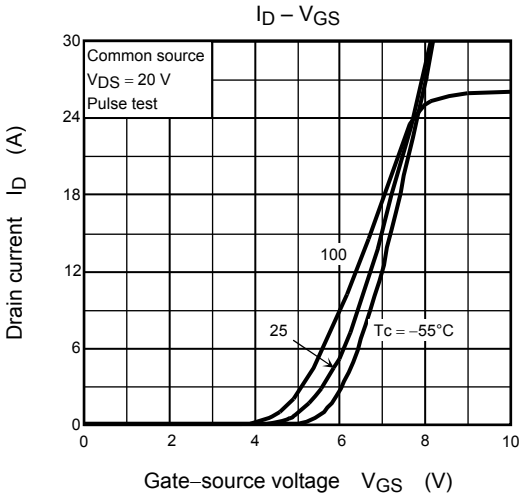
| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Continuous drain reverse current (Note 1) | $I_{DR}$ | — | — | — | 15 | A |
| Pulse drain reverse current (Note 1) | $I_{DRP}$ | — | — | — | 30 | A |
| Forward voltage (diode) | $V_{DSF}$ | $I_{DR}$ = 15 A, $V_{GS}$ = 0 V | — | — | -1.7 | V |
| Reverse recovery time | $t_{rr}$ | $I_{DR}$ = 15 A, $V_{GS}$ = 0 V, | — | 530 | — | ns |
| Reverse recovery charge | $Q_{rr}$ | $dI_{DR}/dt$ = 100 A/μs | — | 9.0 | — | μC |

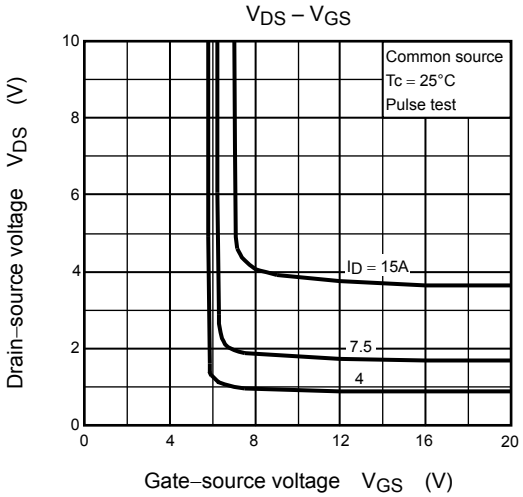
## Marking

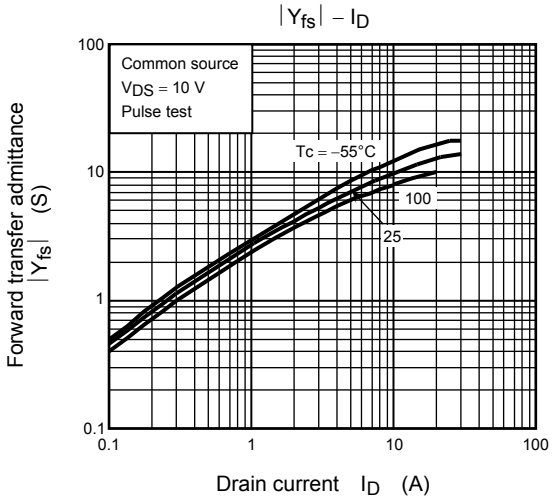


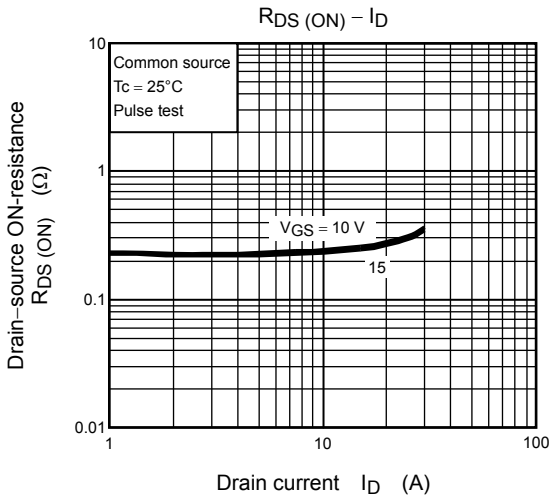

ID – VDS
Common source
Tc = 25°C
Pulse test
10
15
8
7
6.8
6.5
6.2
6
VGS = 5.8 V
Drain current ID (A)
Drain−source voltage VDS (V)


ID – VDS
10
15
8.5
Common source
Tc = 25°C
Pulse test
8
7.5
7
6.3
VGS = 6.2 V
Drain current ID (A)
Drain−source voltage VDS (V)


ID – VGS
Common source
VDS = 20 V
Pulse test
100
25
Tc = −55°C
Drain current ID (A)
Gate−source voltage VGS (V)


VDS – VGS
Common source
Tc = 25°C
Pulse test
ID = 15A
7.5
4
Drain−source voltage VDS (V)
Gate−source voltage VGS (V)


|Yfs| – ID
Common source
VDS = 10 V
Pulse test
Tc = −55°C
100
25
Forward transfer admittance |Yfs| (S)
Drain current ID (A)


RDS (ON) – ID
Common source
Tc = 25°C
Pulse test
VGS = 10 V
15
Drain−source ON-resistance RDS (ON) (Ω)
Drain current ID (A)